

SUBSTRATE PROCESSING APPARATUS AND SUBSTRATE PROCESSING METHOD

ABSTRACT

In one exemplary embodiment, a substrate processing apparatus is provided. The substrate processing apparatus comprises: a chamber; a substrate support disposed in the chamber; a gas supply disposed in the chamber and connected to a supply source of reaction gas containing HF gas and $C_xH_yF_z$ gas (where x and z are integers equal to or greater than 1 and y is an integer equal to or greater than 0); and a plasma-generator configured to form a plasma from the reaction gas supplied to the chamber from the gas supply, wherein at least a portion of the chamber exposed to the plasma is made of a conductive silicon-containing material.

Fig. 1